Vishay Siliconix

Powered-off Protection, High Speed, 1.65 V to 5.5 V, SPDT Analog Switch (2:1 Multiplexer / Demultiplexer Bus Switch)

DESCRIPTION

The DG3157E is a high speed single-pole double-throw analog switch designed for +1.65 V to +5.5 V single power rail operation.

Fabricated with high density CMOS technology, the DG3157E achieves low on-resistance, fast switching speed, and high bandwidth while maintains low power consumption.

The DG3157E can handle both analog and digital signals and permits signals with amplitudes of up to V+ to be transmitted in either direction.

When the select pin is low, B_0 is connected to the output A pin. When the select pin is high, B_1 is connected to the output A pin. The path that is open will have a high impedance state with respect to the output. Break before make switching performance is guaranteed.

A powered-off protection circuit is built into the switch to prevent an abnormal current flow from COM pin to V+ during the power-down condition. Each output pin can withstand greater than 7 kV (human body model).

Operation temperature is specified from -40 $^{\circ}$ C to +85 $^{\circ}$ C. The DG3157E is available in the compact SC-70-6L package.

FEATURES

 Direct cross to industry standard SN74LVC1G3157, NC7SB3157, NLASB3157, PI5A3157, and STG3157



ROHS COMPLIANT HALOGEN

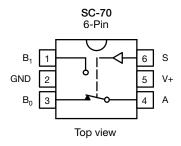
FREE

- Low switch on-resistance (6 Ω)
- +1.65 V to +5.5 V single supply operation
- Powered-off protection
- Control logic inputs can go over V+ up to 5.5 V
- · Low parasitic capacitance, 7 pF at switch off
- · Break before make switching
- Latch-up performance exceeds 200 mA per JESD 78
- · High ESD rating
 - 7000 V human body model (JS-001)
 - 1000 V charge device model (JS-002)
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- · Battery powered devices
- · Consumer and computing
- Instrumentation
- Medical equipment
- · Control and automation

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Device marking: H0

TRUTH TABLE	
LOGIC INPUT (S)	FUNCTION
0	B ₀ connected to A
1	B ₁ connected to A

ORDERING INFORMATION					
TEMP. RANGE	PACKAGE	PART NUMBER			
-40 °C to +85 °C	SC-70-6	DG3157EDL-T1-GE3 (halogen-free)			

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ABSOLUTE MAXIMUM RATINGS						
PARAMETER		LIMIT	UNIT			
V+, A, B ₀ , B ₁ , S reference to GND		-0.3 to 6	V			
Continuous current (any terminal)		± 50	mA			
Peak current (pulsed at 1 ms, 10 % duty cycle)		± 200	T IIIA			
Storage temperature	D suffix	-65 to +150	°C			
Power dissipation (packages) ^a	6-pin SC-70 b	250	mW			
ESD / HBM	JS-001	7000	V			
ESD / CDM	JS-002	1000	V			
Latch up	Per JESD78 with 1.5 x V _{abs} max. clamp	200	mA			

Notes

- a. All leads welded or soldered to PC board b. Derate 3.1 mW/°C above 70 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS									
		TEST CONDITIONS UNLESS OTHERWISE SPECIFIED $V_S = 0.25 \text{ V+ or } 0.75 \text{ V+, V+} = 1.65 \text{ V to } 1.95 \text{ V}^e$		TEMP.a	LIMITS				
PARAMETER	SYMBOL					°C to +8		UNIT	
		$V_S = 0.2 \text{ V+ or } 0.6$	65 V+, V+ = 2.3 V to 5.5 V ^e		MIN. b	TYP. c	MAX. b		
DC Characteristics		1							
High level input voltage	V _{SH}		1.65 V to 1.95 V	Full	0.75 V+	-	-		
I light level lipat veltage	*511	V+ = 2.3 V to 5.5 V		Full	0.65 V+	-	-	V	
Low level input voltage	V_{SL}		1.65 V to 1.95 V	Full	-	-			
	· SL	V+ =	2.3 V to 5.5 V	Full	-	-	-	<u> </u>	
			$V_{BN} = 0 \text{ V}, I_A = 30 \text{ mA}$	Full	-	8	11		
		V+ = 4.5 V	$V_{BN} = 2.3 \text{ V}, I_{A} = -30 \text{ mA}$	Full	-	6			
			$V_{BN} = 4.5 \text{ V}, I_{A} = -30 \text{ mA}$	Full	-	7			
		V+ = 3 V	$V_{BN} = 0 \text{ V}, I_{A} = 24 \text{ mA}$	Full	-	10			
On resistance	R _{ON}	V1 = 0 V	$V_{BN} = 3 \text{ V}, I_{A} = -24 \text{ mA}$	Full	-	9	• =]	
		V+ = 2.3 V	$V_{BN} = 0 \text{ V}, I_{A} = 8 \text{ mA}$	Full	-	13			
		V+ = 2.5 V	$V_{BN} = 2.3 \text{ V}, I_{A} = -8 \text{ mA}$	Full	-	12			
		V+ = 1.65 V	$V_{BN} = 0 \text{ V}, I_{A} = 4 \text{ mA}$	Full	-	20			
			$V_{BN} = 1.65 \text{ V}, I_A = -4 \text{ mA}$	Full	-	18	23	Ω	
	R _{FLAT}	0 < V _{BN} < V+	$V+ = 4.5 \text{ V}, I_A = -30 \text{ mA}$	Room	-	2	-		
On resistance flatness			$V+ = 3 V, I_A = -24 mA$	Room	-	4	-		
0.1.100.010.100			$V+ = 2.3 \text{ V}, I_A = -8 \text{ mA}$	Room	-	10	-		
			$V+ = 1.65 \text{ V}, I_A = -4 \text{ mA}$	Room	-	58	-		
			$_{BN} = 3.15 \text{ V}, I_{A} = -30 \text{ mA}$	Room	-	0.09	-		
On resistance matching	ΔR_{ON}	V+ = 3 V, V _{BN} = 2.1 V, I _A = -24 mA V+ = 2.3 V, V _{BN} = 1.6 V, I _A = -8 mA		Room	-	0.13	-		
between channels				Room	-	0.15	-		
		V+ = 1.65 V, \	$I_{BN} = 1.15 \text{ V}, I_{A} = -4 \text{ mA}$	Room	-	0.16	95 °C MAX. b 0.25 V+ 0.2 V+ 11 9 9 14 12 18 16 26 23		
Input leakage current	Is	V+ = 5.5 V, V _S = 5.5 V		Room	-0.1	-	0.1		
mpar ioanago oarrone	'5			Full	-1	-	-]	
Off stage switch leakage	I _{BN(off)}	$V+ = 5.5 \text{ V}, V_A = 1 \text{ V} / 4.5 \text{ V}, V_B = 4.5 \text{ V} / 1 \text{ V}$		Room	-0.1	-	0.1		
on stage switch realtage	'BIN(OII)	V1 = 0.0 V, V _A =	V+ = 5.5 V, VA = 1 V / 4.5 V, VB = 4.5 V / 1 V		-1	-		μA	
On state switch leakage	I _{BN(on)}	$V+ = 5.5 \text{ V}, V_A = V_B = 1 \text{ V or } 4.5 \text{ V}$		Room Full	-0.1	-		μ, ,	
	i DIN(OH)	,	, , , <u> </u>		-1	-			
Power down leakage	I _{PD}		$V, B_0, B_1 \text{ open}, V_S = GND$	Full	-	-			
· ·	טאי	$V+ = 0 V, V_{B0}, V_{B}$	$s_1 = 5 \text{ V}, \text{ A open}, \text{ V}_S = \text{GND}$	Full	-	-	5		
Power Supply	1	·		ı	1				
Power supply range	V+			Full	1.65	-		V	
Quiescent supply current	l+	$V+ = 5.5 V$, $V_S = V+ or GND$		Room	-	-		μA	
Quiescent supply current				Full	-	-	5	μΛ	



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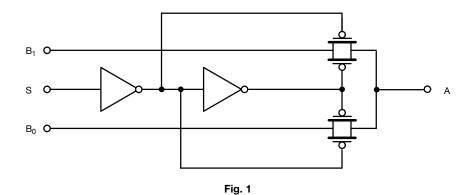
SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED		TEMP.a	LIMITS -40 °C to +85 °C			UNIT
	01111202	$V_S = 0.25 \text{ V+ or } 0.79 \text{ V}_S = 0.2 \text{ V+ or } 0.69 \text{ V}_S = 0.2 \text{ V+ or } 0.69 \text{ V}_S = 0.2 \text{ V+ or } 0.69 \text{ V}_S = 0.2 \text{ V+ or } 0.69 \text{ V}_S = 0.20 \text{ V+ or } 0.69 \text{ V}_S = 0.20 \text{ V+ or } 0.69 \text{ V+ or } $	5 V+, V+ = 1.65 V to 1.95 V e 65 V+, V+ = 2.3 V to 5.5 V e		MIN. b	TYP. c	MAX. b	
AC Electrical Characterist	tics ^e			•				
		V _A = 0 V, see Fig. 3	V+ = 1.65 V to 1.95 V	Full	-	4	-	
Duan dalau tima f	t _{PHL} /t _{PLH}		V+ = 2.3 V to 2.7 V	Full	-	3	-	
Prop delay time ^f			V+ = 3 V to 3.6 V	Full	-	2	-	
			V+ = 4.5 V to 5.5 V	Full	1	2	-	
			V+ = 1.65 V to 1.95 V	Room	1	32	1	
			V+ = 1.05 V to 1.95 V	Full	-	34	-	
		$\begin{split} V_{LOAD} &= 2 \text{ x V+} \\ \text{for } t_{PZL}, \\ V_{LOAD} &= 0 \text{ V} \\ \text{for } t_{PZH}, \\ \text{see Fig. 4} \end{split}$	V+ = 2.3 V to 2.7 V	Room	-	22	-	ns
Output enable time f	t _{PZI} /t _{PZH}		V+ = 2.3 V tO 2.7 V	Full	1	23	1	
Output enable time	'PZL/'PZH		V+ = 3 V to 3.6 V	Room	-	19	-	
			V+ = 3 V 10 3.0 V	Full	-	20	-	
			V+ = 4.5 V to 5.5 V	Room	-	16	-	
			V+ = 4.5 V to 5.5 V	Full	-	16	-	
	t _{PLZ} /t _{PHZ}	$V_{LOAD} = 2 \times V_{+}$ for t_{PLZ} , $V_{LOAD} = 0 V$ for t_{PHZ} , see Fig. 4	V+ = 1.65 V to 1.95 V	Room	-	22	-	
				Full	-	23	-	
			V+ = 2.3 V to 2.7 V	Room	-	18	-	
Output disable time ^f				Full	1	19	-	
Output disable time			V+ = 3 V to 3.6 V	Room	1	16	ı	
				Full	1	16	-	
			V+ = 4.5 V to 5.5 V	Room	1	13	ı	
				Full	1	14	1	
		V+ = 1	1.65 V to 1.95 V	Full	0.5	-	-	
Break-before-make time d	t _{BBM}	V+ = 2.3 V to 2.7 V		Full	0.5	-	ı	<u> </u>
break-belore-make time		V+ = 3 V to 3.65 V		Full	0.5	-	ı	
		V+ =	V+ = 4.5 V to 5.5 V		0.5	-	ı	
	Q	$C_L = 0.1 \text{ nF},$ $V_{GEN} = 0 \text{ V}$ $R_{GEN} = 0 \Omega$	V+ = 5 V	Room	1	1.3	ı	
Charge injection ^d			V+ = 3.3 V	Room	-	0.5	-	рС
Analog Switch Characteri	stics			•				
Off isolation d	OIRR	D 5	0.0.f. 10.MU=	Room	-	-61	=	٩D
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $f = 10 MHz$		Room	-	-61	-	dB
-3 dB bandwidth ^d	BW	$R_L = 50 \Omega$		Room	1	580	-	MHz
Capacitance								
Control pin capacitance d	C _{IN}		V+ = 0 V	Room	-	6	-	
B port off capacitance d	C _{IO-B}	V+ = 5 V		Room	1	7	-	pF
A port capacitance when switch enable ^d	C _{IO-A(on)}			Room	-	12	-	ρ,

Notes

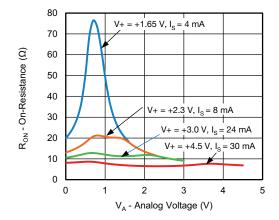
- a. Room = 25 °C, full = as determined by the operating suffix
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- c. Typical values are for design aid only, not guaranteed nor subject to production testing
- d. Guarantee by design, nor subjected to production test
- e. V_S = input voltage to perform proper function
- f. Guaranteed by design and not production tested. The bus switch propagation delay is a function of the RC time constant contributed by the on-resistance and the specified load capacitance with an ideal voltage source (zero output impedance) driving the switch



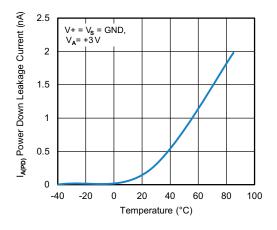
LOGIC DIAGRAM POSITIVE LOGIC



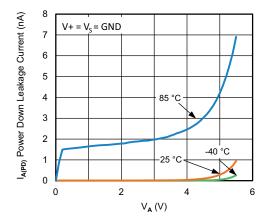
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



R_{ON} vs. V_A vs. V+



Power Down Leakage Current vs. Temperature



Power Down Leakage Current vs. V_A



AC LOADING AND WAVEFORMS

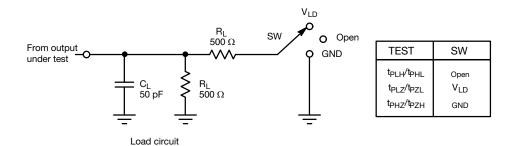


Fig. 2 - AC Test Circuit

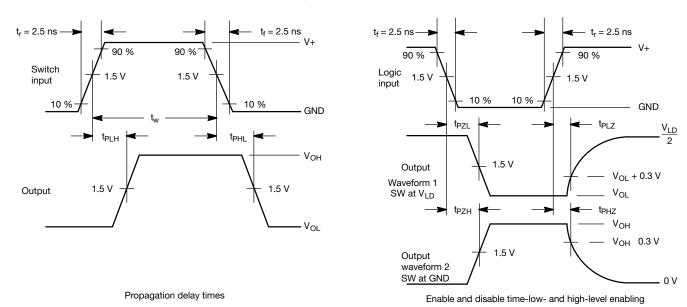


Fig. 3 - AC Waveforms

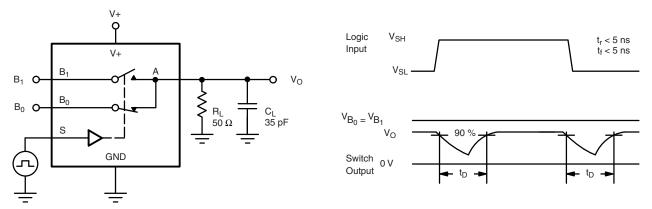
Fig. 4 - AC Waveforms

Notes

- C_L includes probe and jig capacitance
- Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control
- Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω
- · The outputs are measured one at a time with one transition per measurement
- t_{PLZ} and t_{PHZ} are the same as t_{dis}
- t_{PZL} and t_{PZH} are the same as t_{dis}
- t_{PLH} and t_{PHL} are the same as t_{dis}
- V_{LD} = 2 V+



TEST CIRCUITS



C_L (includes fixture and stray capacitance)

Fig. 5 - Break-Before-Make Interval

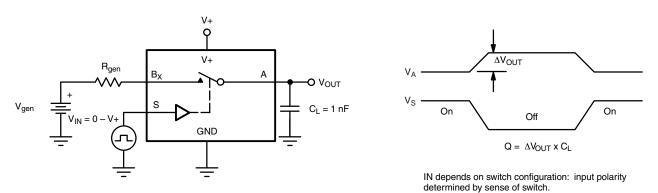


Fig. 6 - Charge Injection

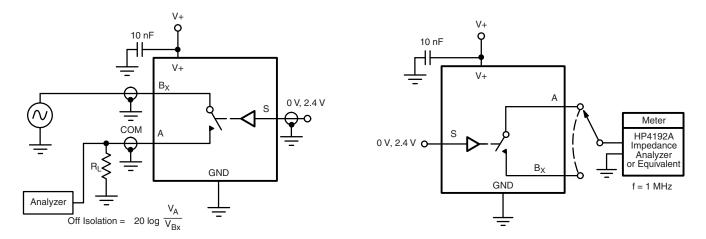


Fig. 7 - Off-Isolation

S18-0421-Rev. C, 23-Apr-18

Fig. 8 - Channel Off/On Capacitance

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